



1N70

Power MOSFET

1.2 Amps, 700 Volts N-CHANNEL MOSFET

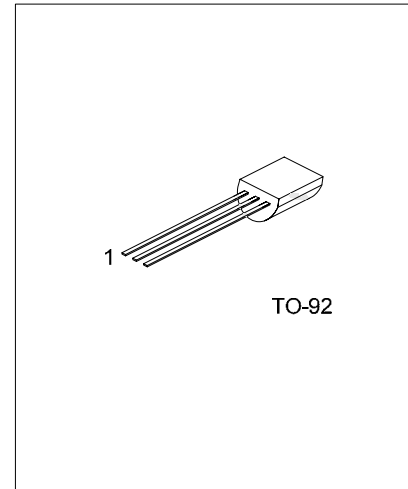
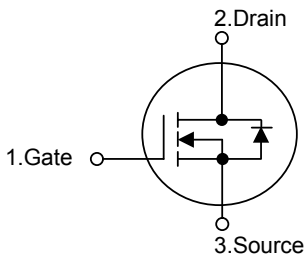
DESCRIPTION

The UTC 1N70 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} = 11.5\Omega @ V_{GS} = 10V$.
- * Ultra Low gate charge (typical 5.0nC)
- * Low reverse transfer capacitance ($C_{RSS} =$ typical 3.0 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



*Pb-free plating product number: 1N70L

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
1N70-T92-B	1N70L-T92-B	TO-92	G	D	S	Tape Box
1N70-T92-K	1N70L-T92-K	TO-92	G	D	S	Bulk

<p>1N70L-T92-B</p> <p>(1)Packing Type (2)Package Type (3)Lead Plating</p>	<p>(1) B: Tape Box, K: Bulk, T: Tube, R: Tape Reel (2) T92: TO-92 (3) L: Lead Free Plating, Blank: Pb/Sn</p>
---	--

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 1)		I_{AR}	1.2	A
Continuous Drain Current		I_D	1.2	A
Pulsed Drain Current (Note 1)		I_{DM}	4.8	A
Avalanche Energy	Single Pulsed (Note 2)	E_{AS}	50	mJ
	Repetitive (Note 1)	E_{AR}	4.0	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5	V/ns
Power Dissipation		P_D	3	W
Junction Temperature		T_J	+150	
Operating Temperature		T_{OPR}	-55 ~ +150	
Storage Temperature		T_{STG}	-55 ~ +150	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction-to-Ambient	θ_{JA}	79	/W
Junction-to-Case	θ_{Jc}	29	/W

■ ELECTRICAL CHARACTERISTICS (T_C=25 °C, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	700			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS} V _{GS} = 30V, V _{DS} = 0V V _{GS} = -30V, V _{DS} = 0V			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	BV _{DSS} /T _J	I _D = 250μA		0.4		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 0.6A		9.3	11.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1MHz		120	150	pF
Output Capacitance	C _{OSS}			20	25	pF
Reverse Transfer Capacitance	C _{RSS}			3.0	4.0	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =300V, I _D =1.2A, R _G =50Ω (Note 4,5)		5	20	ns
Turn-On Rise Time	t _R			25	60	ns
Turn-Off Delay Time	t _{D(OFF)}			7	25	ns
Turn-Off Fall Time	t _F			25	60	ns
Total Gate Charge	Q _G	V _{DS} =480V, V _{GS} =10V, I _D =1.2A (Note 4,5)		5.0	6.0	nC
Gate-Source Charge	Q _{GS}			1.0		nC
Gate-Drain Charge	Q _{GD}			2.6		nC
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S = 1.2A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				1.2	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				4.8	A
Reverse Recovery Time	t _{RR}	V _{GS} =0V, I _S = 1.2A		160		ns
Reverse Recovery Charge	Q _{RR}	di _F /dt = 100A/μs (Note1)		0.3		μC

- Note:
1. Repetitive Rating: Pulse width limited by maximum junction temperature
 2. L = 60mH, I_{AS} = 1A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
 3. I_{SD} ≤ 1.2A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
 4. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
 5. Essentially Independent of Operating Temperature

■ TEST CIRCUITS AND WAVEFORMS

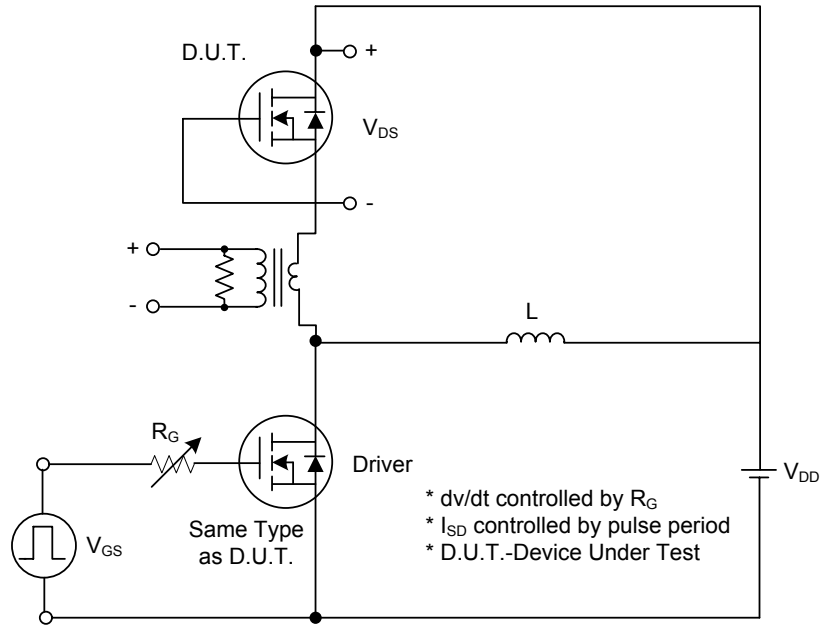


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

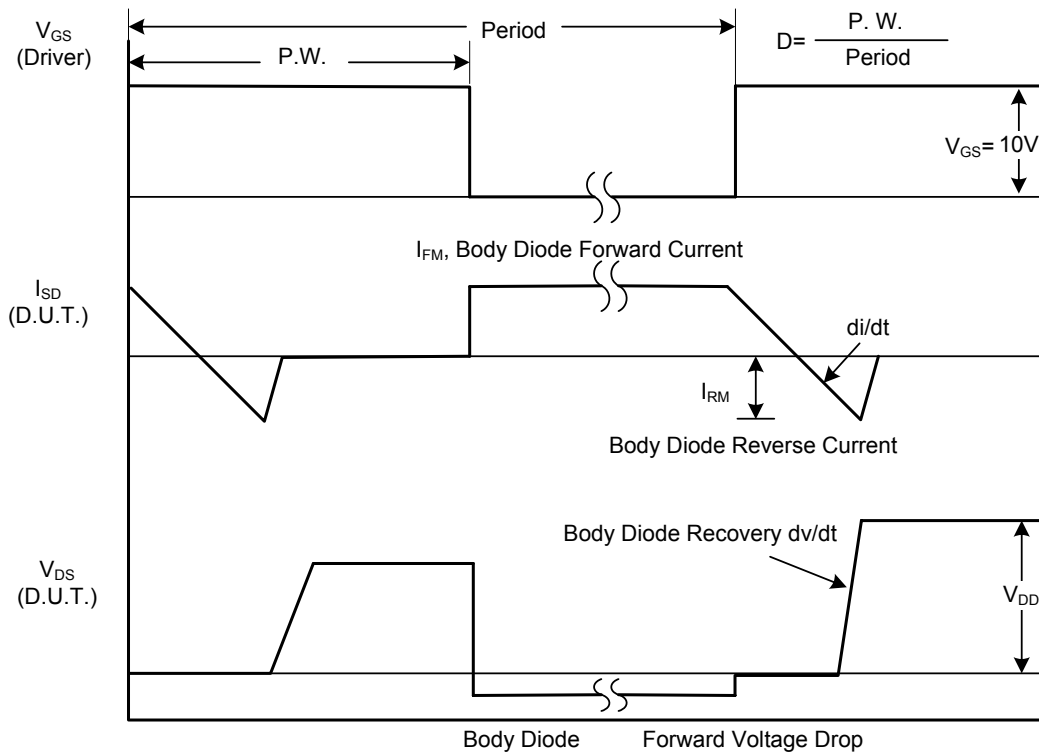


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

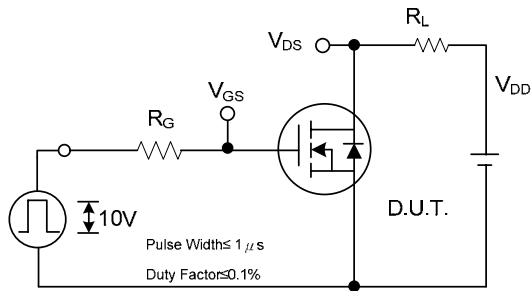


Fig. 2A Switching Test Circuit

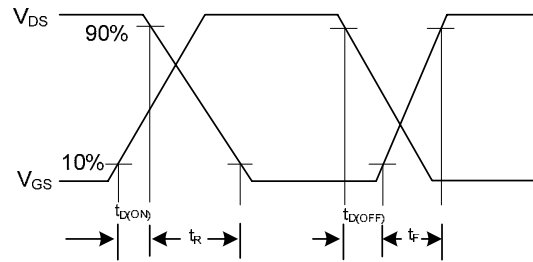


Fig. 2B Switching Waveforms

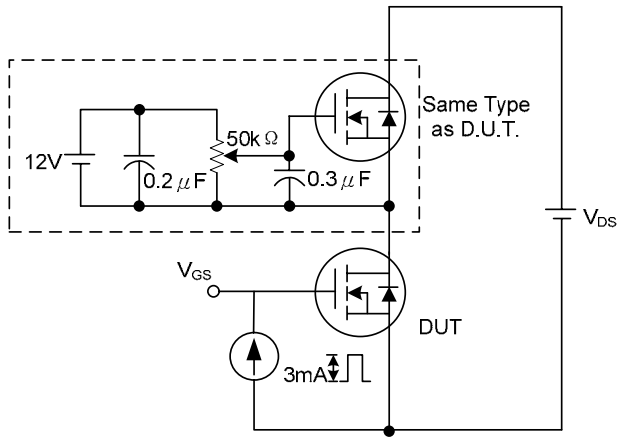


Fig. 3A Gate Charge Test Circuit

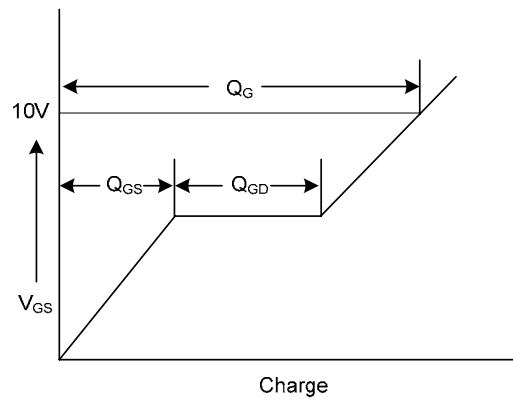


Fig. 3B Gate Charge Waveform

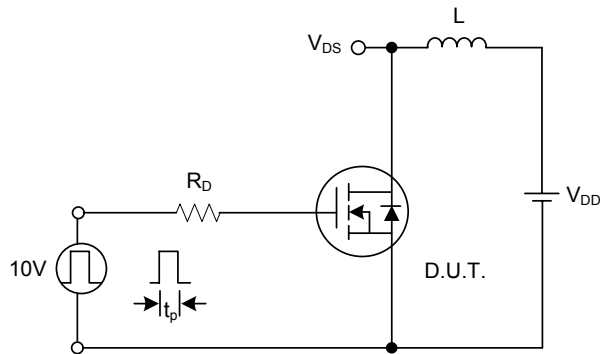


Fig. 4A Unclamped Inductive Switching Test Circuit

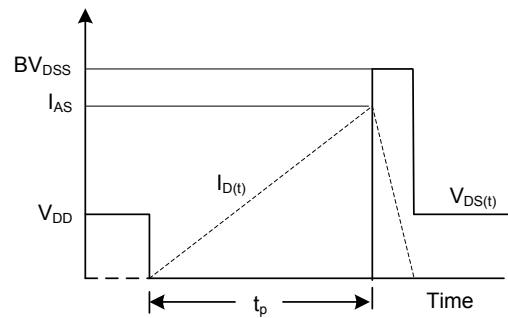
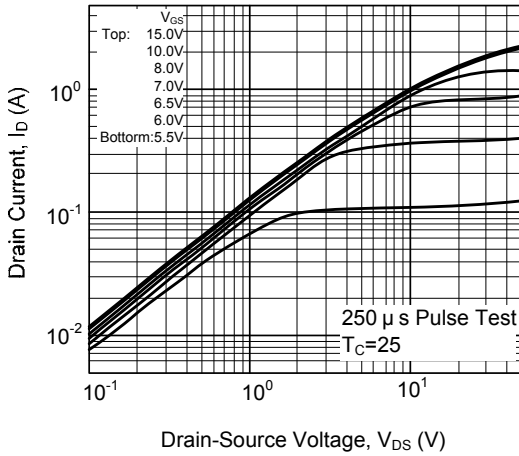


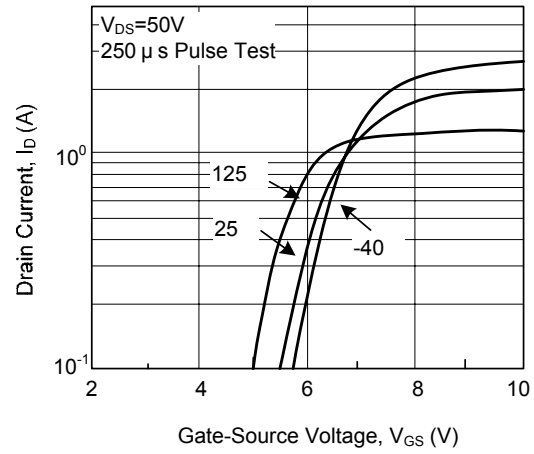
Fig. 4B Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS

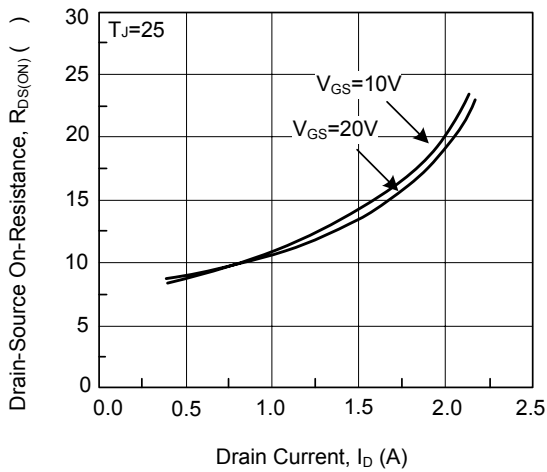
Output Characteristics



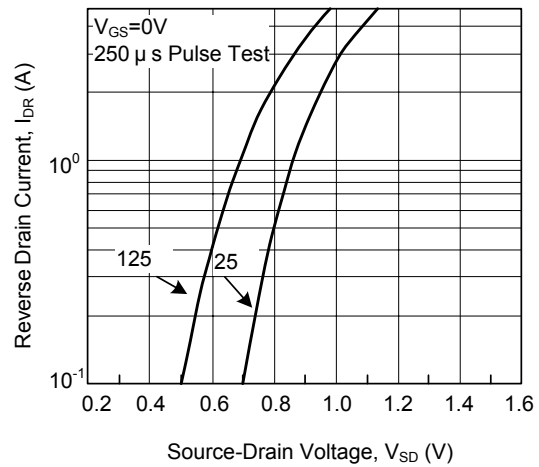
Transfer Characteristics



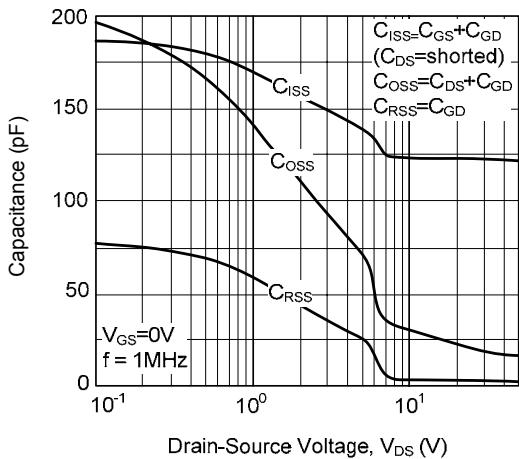
On-Resistance vs. Drain Current



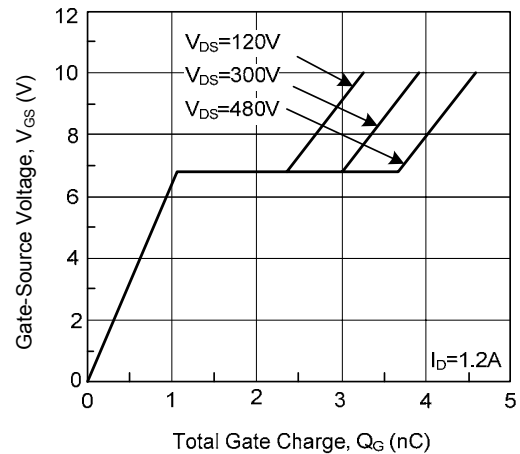
Source- Drain Diode Forward Voltage



Capacitance vs. Drain-Source Voltage

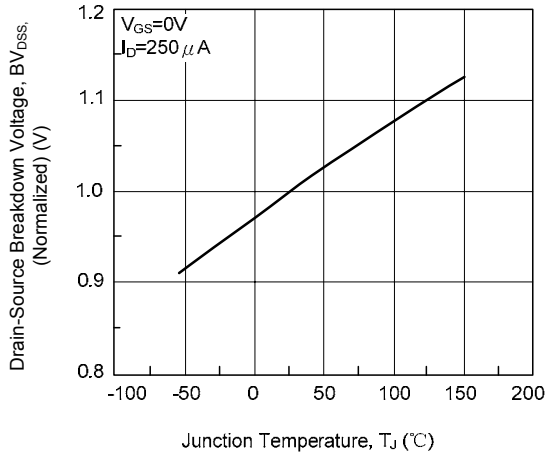


Gate Charge vs. Gate-Source Voltage

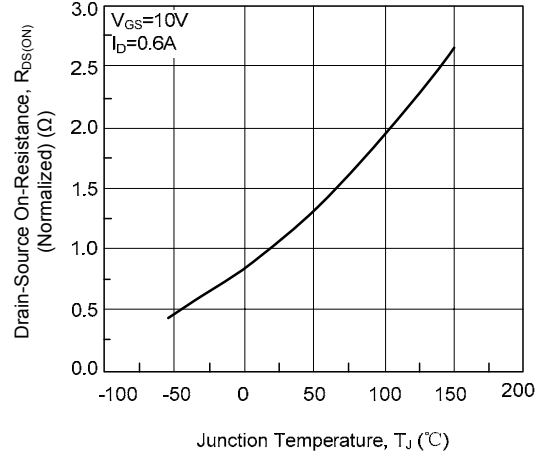


TYPICAL CHARACTERISTICS(Cont.)

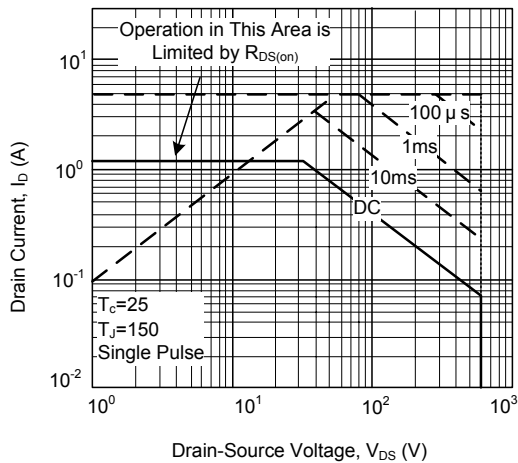
Breakdown Voltage vs. Temperature



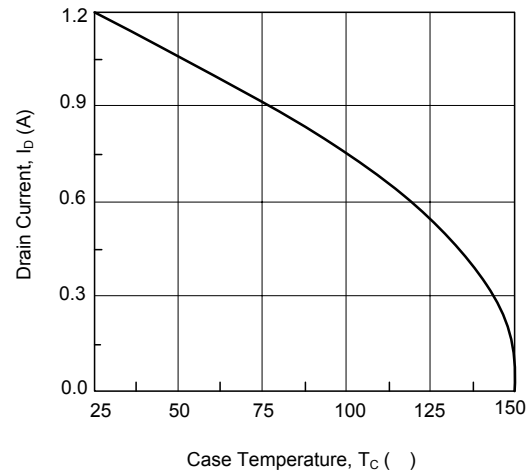
On-Resistance vs. Temperature



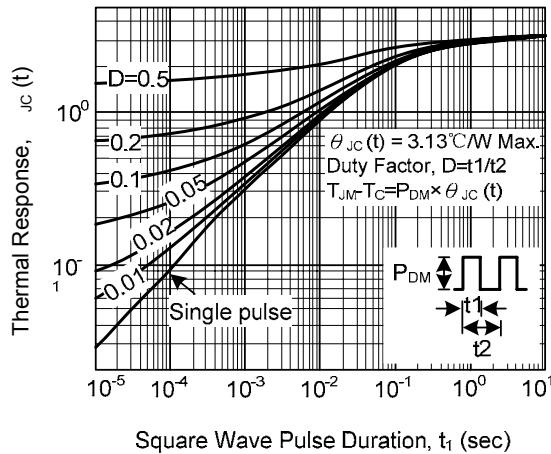
Max. Safe Operating Area



Max. Drain Current vs. Case Temperature



Thermal Response



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

